

HCC4011B/12B/23B HCF4011B/12B/23B

NAND GATES

QUAD 2 INPUT HCC/HCF 4011B DUAL 4 INPUT HCC/HCF 4012B TRIPLE 3 INPUT HCC/HCF 4023B

- PROPAGATION DELAY TIME = 60ns (typ.) AT C_L = 50pF, V_{DD} = 10V
- BUFFERED INPUTS AND OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDECTENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

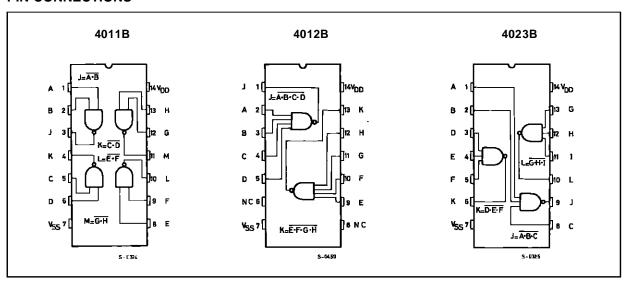
EY (Plastic Package) (Ceramic Frit Seal Package) M1 C1 (Micro Package) (Plastic Chip Carrier) ORDER CODES: HCC40XXBF HCF40XXBM1 HCF40XXBEY HCF40XXBC1

DESCRIPTION

The HCC4011B, HCC4012B and HCC4023B (extended temperature range) and HCF4011B, HCF4012B and HCF4023B (intermediate temperature range) are monolithic, integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The HCC/HCF4011B, HCC/HCF4012B and HCC/HCF4023B NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of COS/MOS gates. All inputs and outputs are buffered.

PIN CONNECTIONS



June 1989 1/12

ABSOLUTE MAXIMUM RATINGS

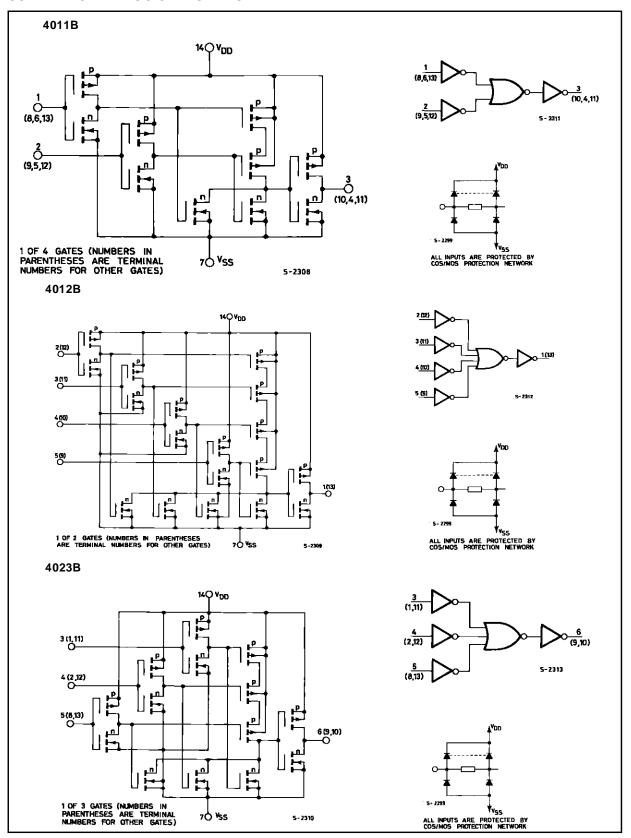
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	< < < < < < < < < < < < < < < < < <
Vi	Input Voltage	- 0.5 to V _{DD} + 0.5	V
$I_{\rm I}$	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package-temperature Range	200 100	mW mW
Тор	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	ပ္
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Parameter	Value	Unit
Supply Voltage: HCC Types	3 to 18	V
HCF Types	3 to 15	V
Input Voltage	0 to V _{DD}	V
Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C
	Supply Voltage : HCC Types HCF Types Input Voltage	Supply Voltage : HCC Types 3 to 18 HCF Types 3 to 15 Input Voltage 0 to V _{DD} Operating Temperature : HCC Types - 55 to + 125

SCHEMATIC AND LOGIC DIAGRAMS



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

			Т	est Con	dition	s				Value				
Symbol	Parame	ter	Vı	۷o	I ₀	V _{DD}	ΤL	o w*		25°C		T _{Hi}	gh*	Unit
			(V)	(V)	(μA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
ΙL	Quiescent		0/5			5		0.25		0.01	0.25		7.5	
	Current	нсс	0/10			10		0.5		0.01	0.5		15	
		Types	0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	μΑ
			0/ 5			5		1		0.01	1		7.5	
		HCF Types	0/10			10		2		0.01	2		15	
		Турсз	0/15			15		4		0.01	4		30	
V _{OH}	Output High	า	0/5		< 1	5	4.95		4.95			4.95		
	Voltage		0/10		< 1	10	9.95		9.95			9.95		V
			0/15		< 1	15	14.95		14.95			14.95		
V _{OL}	Output Low	1	5/0		< 1	5		0.05			0.05		0.05	
	Voltage		10/0		< 1	10		0.05			0.05		0.05	V
			15/0		< 1	15		0.05			0.05		0.05	
V _{IH}	Input High			0.5/4.5	< 1	5	3.5		3.5			3.5		
	Voltage			1/9	< 1	10	7		7			7		V
				1.5/13.5	< 1	15	11		11			11		
V _{IL}	Input Low			4.5/0.5	< 1	5		1.5			1.5		1.5	
	Voltage			9/1	< 1	10		3			3		3	V
				13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output		0/5	2.5		5	- 2		- 1.6	- 3.2		- 1.15		
	Drive Current	HCC	0/5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
	Current	Types	0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		mA
			0/5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		1117 (
		HCF	0/5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
		Types	0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		
I _{OL}	Output	1100	0/5	0.4		5	0.64		0.51	1		0.36		
	Sink Current	HCC Types	0/10	0.5		10	1.6		1.3	2.6		0.9		
	Current	1 9 000	0/15	1.5		15	4.2		3.4	6.8		2.4		mA
			0/5	0.4		5	0.52		0.44	1		0.36		111/4
		HCF Types	0/10	0.5		10	1.3		1.1	2.6		0.9		
		1 7 703	0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage	HCC Types	0/18	Any In	nut	18		± 0.1		±10 ⁻⁵	± 0.1		± 1	^
	Current	HCF Types	0/15	Any In	ρuι	15		± 0.3		±10 ⁻⁵	± 0.3		± 1	μΑ
Cı	Input Capa			Any In	put					5	7.5			pF

^{*} $T_{LOW} = -55^{\circ}C$ for **HCC** device : $-40^{\circ}C$ for **HCF** device.

^{*} T_{HIGH} = + 125°C for **HCC** device : + 85°C for **HCF** device. The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V with V_{DD} = 15V.

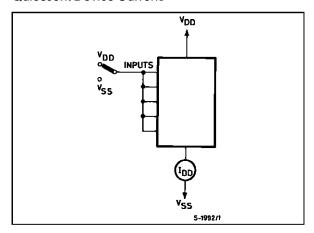


DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50 pF$, $R_{L} = 200 k\Omega$, typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall times = 20ns)

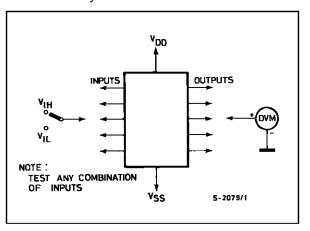
Symbol	Parameter	Test Conditions		Value			Unit
Syllibol	Farameter		V _{DD} (V)	Min.	Тур.	Max.	Oiii
t _{PLH} , t _{PHL}	Propagation Delay Time		5		125	250	
			10		60	120	ns
			15		45	90	
t_{THL}, t_{TLH}	Transition Time		5		100	200	
			10		50	100	ns
			15		40	80	

TEST CIRCUITS

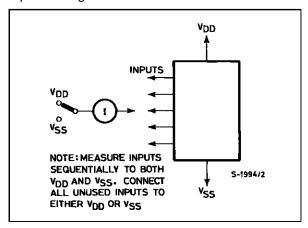
Quiescent Device Current.



Noise Immunity.

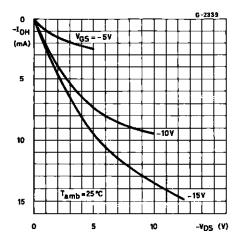


Input Leakage Current.

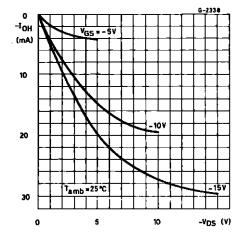


HCC/HFC4011B/12B/23B

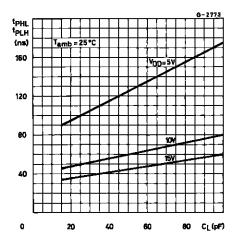
Minimum Output High (source) Current Characteristics.



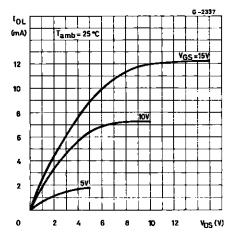
Typical Output High (source) Current Characteristics.



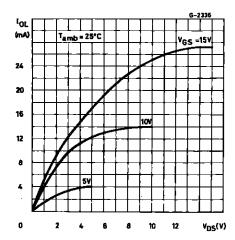
Typical Propagation Delay Time per Gate as a Function of Load Capacitance.



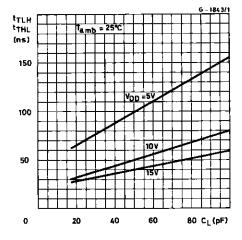
Minimum Output Low (sink) Current Characteristics.



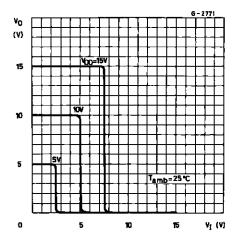
Typical Output Low (sink) Current Characteristics.



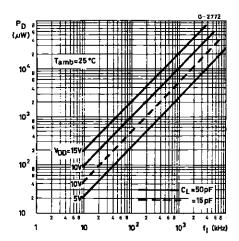
Typical Transition Time vs. Load Capacitance.



Typical Voltage Transfer Characteristics.

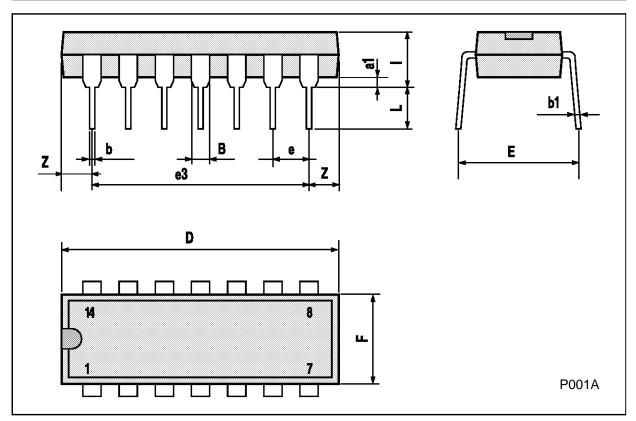


Typical Power Dissipation/gate vs Frequency.



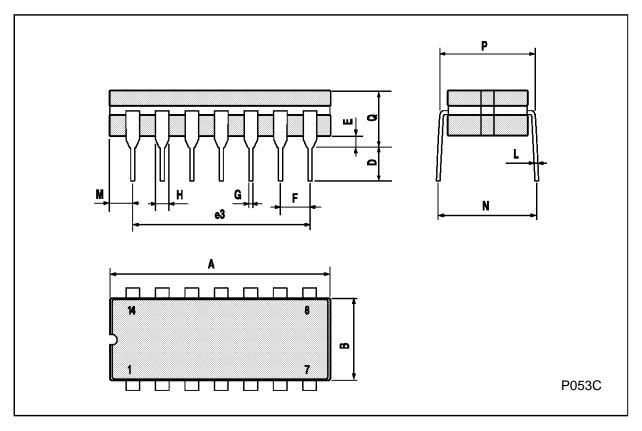
Plastic DIP14 MECHANICAL DATA

DIM.		mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	1.39		1.65	0.055		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		15.24			0.600		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z	1.27		2.54	0.050		0.100	



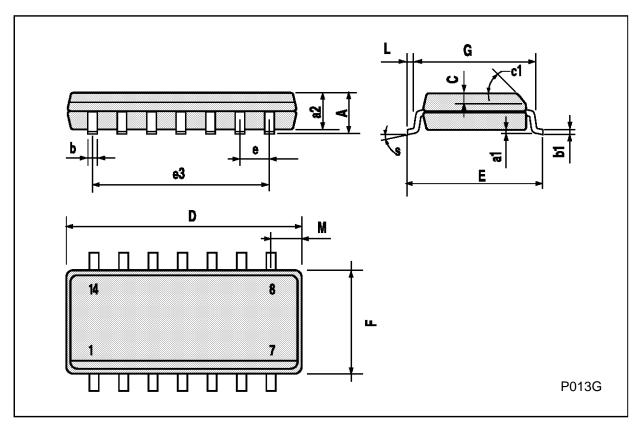
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm		inch		
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			20			0.787
В			7.0			0.276
D		3.3			0.130	
Е	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
Н	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
Р	7.8		8.05	0.307		0.317
Q			5.08			0.200



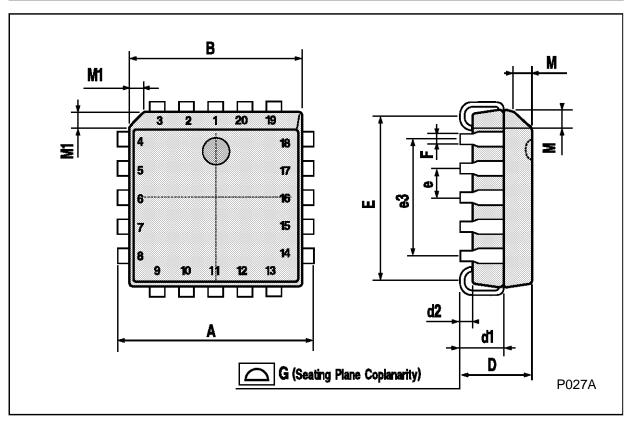
SO14 MECHANICAL DATA

DIM.		mm				
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1		-	45°	(typ.)		
D	8.55		8.75	0.336		0.344
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.68			0.026
S			8° (ı	max.)		



PLCC20 MECHANICAL DATA

DIM.		mm				
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	9.78		10.03	0.385		0.395
В	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
е		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
М		1.27			0.050	
M1		1.14			0.045	



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